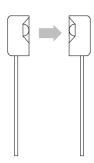
TELEFUNKEN Semiconductors

Matchable Pairs – Emitter and Detector

Description

Pairs of infrared emitting diode and phototransistor, matched in their optical and electrical features. These pairs enable a lot of applications. They can be used both for transmissive or reflective sensor functions. The peak wavelength of the emitter is $\lambda = 950$ nm.



Applications

General for industrial processing and controlling, end of tape detector.

Features

- Miniature case with lens
- Detector with optical filter, protected against ambient light
- Detector case black for easy identification of the emitter and detector
- Emitter-angle of half-intensity $\pm \varphi = 35^{\circ}$
- Detector-angle of half sensitivity $\varphi = 35^{\circ}$
- Emitter and Detector in sideview case
- High CTR $\geq 5\%$

Pin Connection

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Absolute Maximum Ratings

Input (Emitter)

| Parameters | Test Conditions | Symbol | Value | Unit |
|-----------------------|---------------------------|------------------|-------|------|
| Reverse voltage | | V_{R} | 6 | V |
| Forward current | | I_{F} | 60 | mA |
| Forward surge current | $t_p \le 10 \ \mu s$ | I _{FSM} | 1 | A |
| Power dissipation | $T_{amb} \le 25^{\circ}C$ | P_{V} | 100 | mW |
| Junction temperature | | T _i | 100 | °C |

Output (Detector)

| Parameters | Test Conditions | Symbol | Value | Unit |
|---------------------------|--------------------------------------|------------------|-------|------|
| Collector emitter voltage | | V_{CEO} | 70 | V |
| Emitter collector voltage | | V _{ECO} | 7 | V |
| Collector current | | I _C | 50 | mA |
| Collector peak current | $t_p/T = 0.5, t_p \le 10 \text{ ms}$ | I _{CM} | 100 | mA |
| Power dissipation | $T_{amb} \le 25^{\circ}C$ | P _V | 150 | mW |
| Junction temperature | | Ti | 100 | °C |

Coupler

| Parameters | Test Conditions | Symbol | Value | Unit |
|-----------------------------|-----------------------------|------------------|-------------|------|
| Operating temperature range | | T _{amb} | -55 to +85 | °C |
| Storage temperature range | | T _{stg} | -55 to +100 | °C |
| Soldering temperature | 2 mm from case, $t \le 5$ s | T_{sd} | 260 | °C |

Electrical Characteristics

 $T_{amb} = 25^{\circ}C$

Input (Emitter)

| Parameters | Test Conditions | Symbol | Min. | Тур. | Max. | Unit |
|----------------------|-------------------------|-------------------|------|------|------|------|
| Forward voltage | $I_F = 50 \text{ mA}$ | V_{F} | | 1.25 | 1.6 | V |
| Breakdown voltage | $I_R = 100 \mu A$ | V _(BR) | 5 | | | V |
| Junction capacitance | $V_R = 0$, $f = 1$ MHz | Ci | | 50 | | pF |

Output (Detector)

| Parameters | Test Conditions | Symbol | Min. | Тур. | Max. | Unit |
|-------------------------------------|--|----------------------|------|------|------|------|
| Collector emitter breakdown voltage | $I_C = 1 \text{ mA}$ | V _{(BR)CEO} | 70 | | | V |
| Emitter collector breakdown voltage | $I_C = 100 \mu\text{A}$ | V _{(BR)ECO} | 7 | | | V |
| Collector dark current | $V_{CE} = 25 \text{ V}, I_f = 0,$ E = 0 | I _{CEO} | | | 100 | nA |

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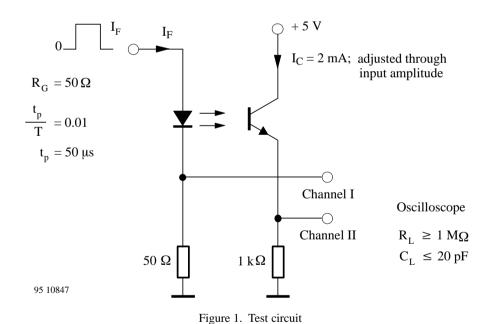
Emitter and Detector matched

| Parameters | Test Conditions | Symbol | Min. | Тур. | Max. | Unit |
|--------------------------------------|---|--------------------|------|------|------|------|
| Collector current | $I_F = 20 \text{ mA}, V_{CE} = 5 \text{ V}$ | I_{C} | 1 | 2 | | mA |
| $I_{\rm C}/I_{\rm F}$ | $I_F = 20 \text{ mA}, V_{CE} = 5 \text{ V}$ | CTR | 0.5 | 1 | | |
| Collector emitter saturation voltage | $\begin{split} I_F &= 20 \text{ mA}, \\ I_C &= 0.1 \text{ mA}, \end{split}$ | V _{CEsat} | | | 0.4 | V |
| Cut-off frequency | $ I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}, $ $ R_L = 100 \Omega $ | f_{C} | | 110 | | kHz |
| Coupling capacitance | f = 1 MHz | C_k | | 0.3 | | pF |

Switching Characteristics

 $V_S = 5 V$

| | Truno | $R_L = 100 \Omega$, see figure 1 | | | | | | $R_L = 1 \text{ k}\Omega$ | | | |
|------|---------------------|-----------------------------------|---------|---------------------|---------------------|-----------------------|---------------------|---------------------------|----------|---------------------|--|
| Type | t _d [μs] | t _r [µs] | ton[µs] | t _s [µs] | t _f [µs] | t _{off} [µs] | I _C [mA] | ton[µs] | toff[µs] | I _F [mA] | |
| | TCZT8012 | | | 10 | | | 8 | 2 | | | |



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TCZT8012

TELEFUNKEN Semiconductors

Ozone Depleting Substances Policy Statement

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

TEMIC TELEFUNKEN microelectronic GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423

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